



M29F200T M29F200B

2 Mbit (256Kb x8 or 128Kb x16, Boot Block) Single Supply Flash Memory

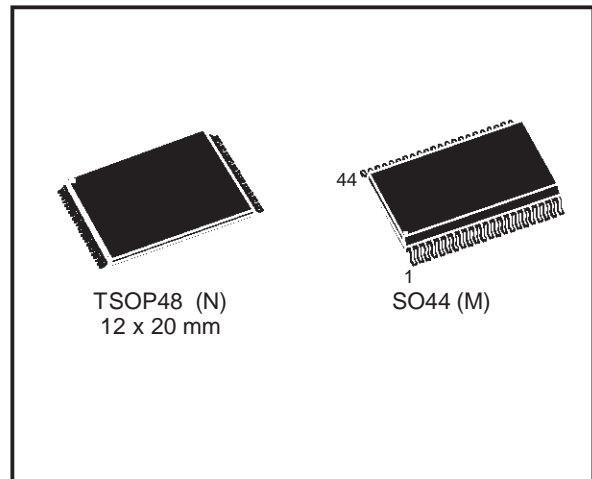
DATA BRIEFING

- 5V±10% SUPPLY VOLTAGE for PROGRAM, ERASE and READ OPERATIONS
- FAST ACCESS TIME: 55ns
- FAST PROGRAMMING TIME
 - 10µs by Byte / 16µs by Word typical
- PROGRAM/ERASE CONTROLLER (P/E.C.)
 - Program Byte-by-Byte or Word-by-Word
 - Status Register bits and Ready/Busy Output
- MEMORY BLOCKS
 - Boot Block (Top or Bottom location)
 - Parameter and Main blocks
- BLOCK, MULTI-BLOCK and CHIP ERASE
- MULTI-BLOCK PROTECTION/TEMPORARY UNPROTECTION MODES
- ERASE SUSPEND and RESUME MODES
 - Read and Program another Block during Erase Suspend
- LOW POWER CONSUMPTION
 - Stand-by and Automatic Stand-by
- 100,000 PROGRAM/ERASE CYCLES per BLOCK
- 20 YEARS DATA RETENTION
 - Defectivity below 1ppm/year
- ELECTRONIC SIGNATURE
 - Manufacturer Code: 0020h
 - Device Code, M29F200T: 00D3h
 - Device Code, M29F200B: 00D4h

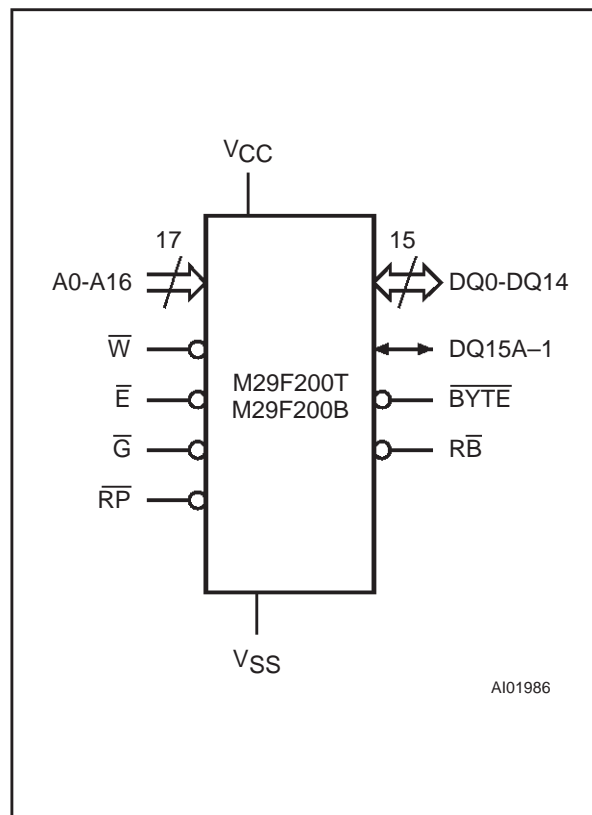
DESCRIPTION

The M29F200 is a non-volatile memory that may be erased electrically at the block or chip level and programmed in-system on a Byte-by-Byte or Word-by-Word basis using only a single 5V V_{CC} supply. For Program and Erase operations the necessary high voltages are generated internally. The device can also be programmed in standard programmers.

The array matrix organisation allows each block to be erased and reprogrammed without affecting other blocks. Blocks can be protected against programming and erase on programming equipment, and temporarily unprotected to make changes in the application.

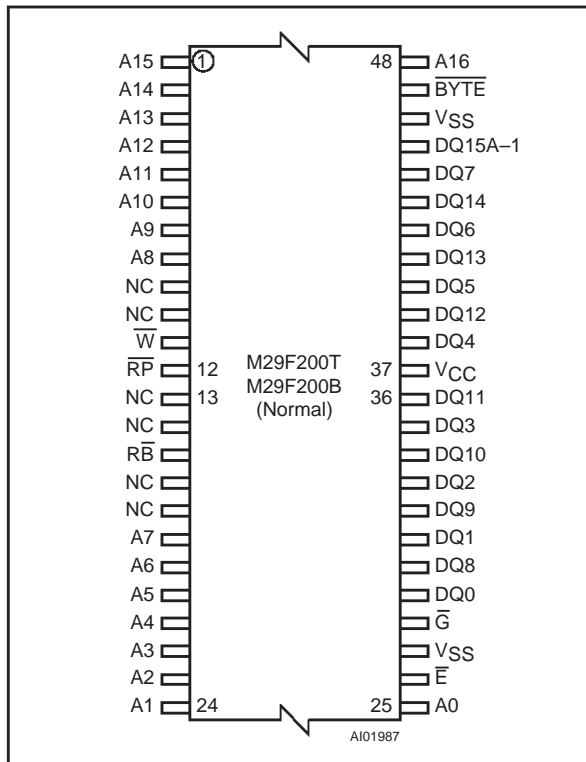


Logic Diagram



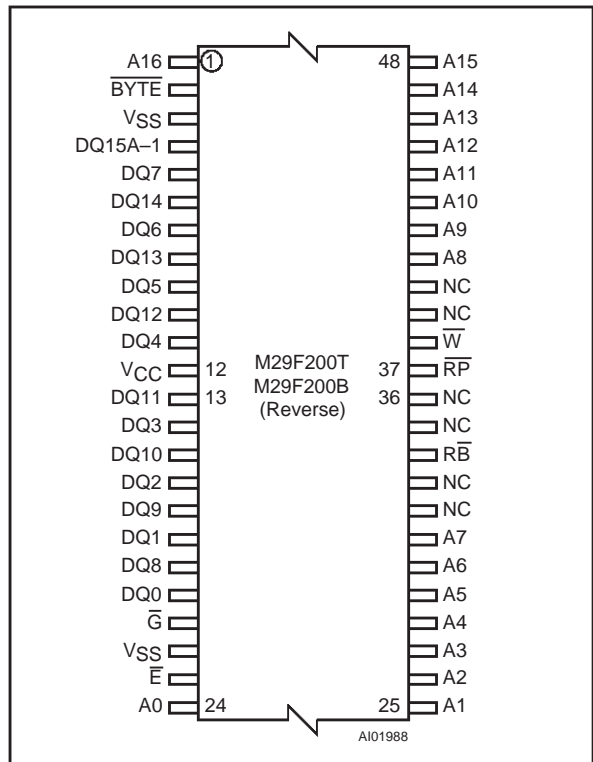
M29F200T, M29F200B

TSOP Pin Connections



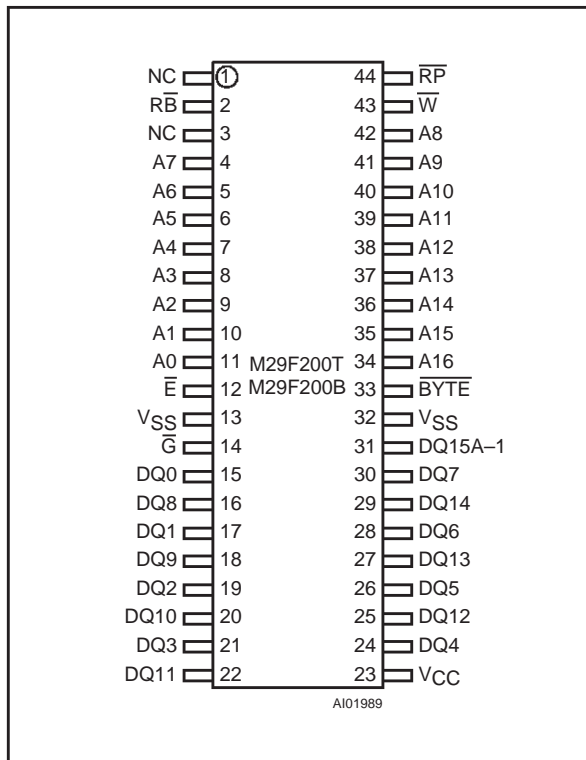
Warning: NC = Not Connected.

TSOP Reverse Pin Connections



Warning: NC = Not Connected.

SO Pin Connections

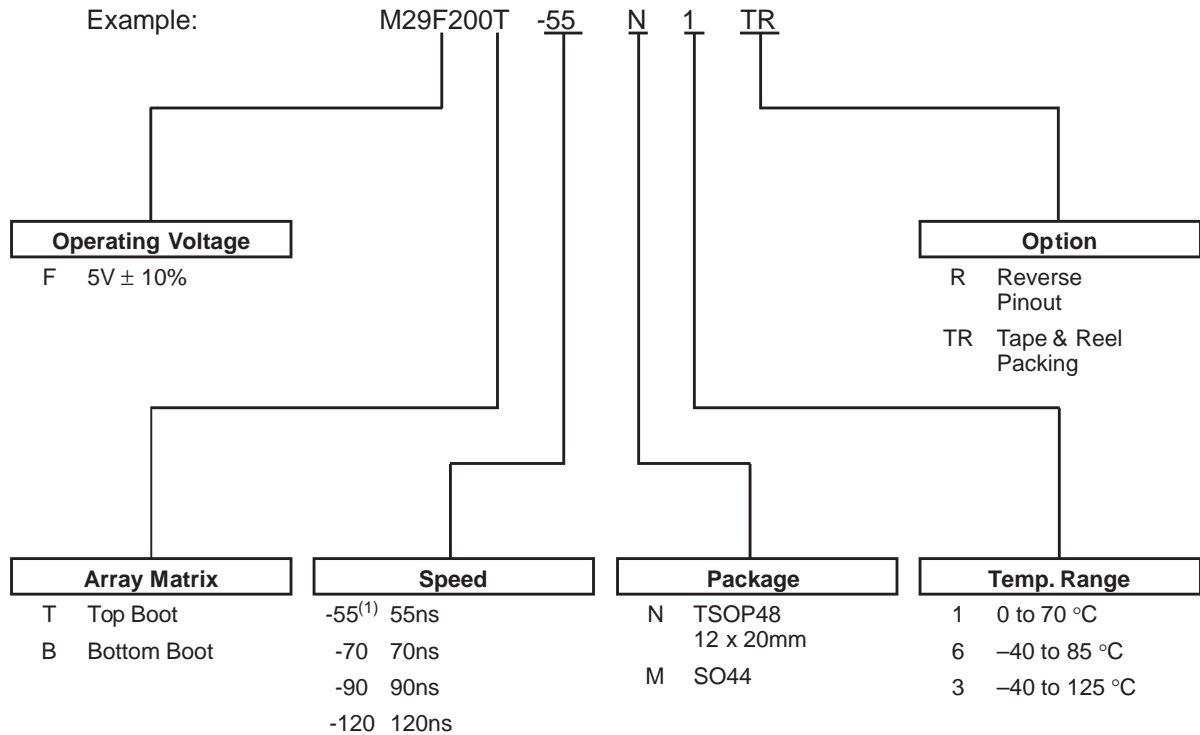


Warning: NC = Not Connected.

Signal Names

A0-A16	Address Inputs
DQ0-DQ7	Data Input/Outputs, Command Inputs
DQ8-DQ14	Data Input/Outputs
DQ15A-1	Data Input/Output or Address Input
\overline{E}	Chip Enable
\overline{G}	Output Enable
\overline{W}	Write Enable
\overline{RP}	Reset / Block Temporary Unprotect
\overline{RB}	Ready/Busy Output
BYTE	Byte/Word Organisation
V _{CC}	Supply Voltage
V _{SS}	Ground

ORDERING INFORMATION SCHEME



Note: 1. Speed obtained with High Speed Measurement Conditions.

Devices are shipped from the factory with the memory content erased (to FFh).

For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.